

RoHS

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### Precision Monolithic Quad SPST CMOS Analog Switches

### DESCRIPTION

The DG1411, DG1412, DG1413 are  $\pm$  15 V precision monolithic quad single-pole single-throw (SPST) CMOS analog switches. Built on a new CMOS process, the Vishay Siliconix DG1411, DG1412, and DG1413 offer low on-resistance of 1.5  $\Omega$ . The low and flat resistance over the full signal range ensures excellent linearity and low signal distortion. The new CMOS platform provides low power dissipation, minimized parasitic capacitance, and low charge injection.

The devices operate from either a single 4.5 V to 24 V power supply, or from dual  $\pm$  4.5 V to  $\pm$  15 V power supplies. The analog switches don't require a V<sub>L</sub> logic supply, while all digital inputs have 0.8 V and 2 V logic thresholds to ensure low-voltage TTL / CMOS compatibility.

The DG1411, DG1412, and DG1413 are bi-directional and support analog signals up to the supply voltage when on, and block them when off. The devices each feature four independently selectable SPST switches. The DG1411 is normally closed, while the DG1412 is normally open. The DG1413 has two normally open and two normally closed switches with guaranteed break-before-make operation.

Combined with fast 100 ns switching times, the improved performance of the DG1411, DG1412, and DG1413 make the devices ideal for signal switching and relay replacement in data acquisition, industrial control and automation, communication, and A/V systems, in addition to medical instrumentation and automated test equipment.

The switches are available in RoHS-compliant, halogen-free TSSOP16 and QFN16 4 mm by 4 mm packages.

#### FEATURES

- 35 V supply max. rating
- On-resistance: 1.5 Ω
- On-resistance flatness: 0.3  $\Omega$
- Channel to channel ON-resistance match: 0.1  $\Omega$
- · Supports single and dual supply operation
- Fully specified at  $\pm$  15 V,  $\pm$  5 V, and +12 V
- Integrated V<sub>L</sub> supply
- 3 V logic compatible
- Low parasitic capacitance: C<sub>S(OFF)</sub>: 11 pF, C<sub>D(ON)</sub>: 87 pF
- Rail to rail signal handling
- Material categorization: For definitions of compliance please see <u>www.vishay.com/doc?99912</u>

**DG1411EQ** 

TSSOP

Top View

16 IN2

14 S2

13

12 N.C

11

10 D3

9 IN3

15 D2

V+

S3

#### BENEFITS

- Low insertion loss
- Low distortion
- Break-before-make switching
- · Low charge injection over the full signal range

#### **APPLICATIONS**

- Medical and Healthcare equipment
- Data acquisition system
- Industrial control and automation
- · Test and measurement equipment
- Communication systems
- · Battery powered systems
- Sample and hold circuits
- Audio and video signal switching

IN1

D1

S1

V-

GND 5

S4

D4

IN4 8

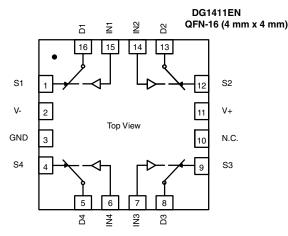
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Relay replacement

#### FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION - DG1411



TRUTH TABLE - DG1411					
LOGIC SWITCH					
0	On				
1	Off				



- QFN EXPOSED PAD TIED TO V-
- N.C. = NO CONNECT
- Switches Shown for Logic "0" Input

S13-2467-Rev. B, 02-Dec-13

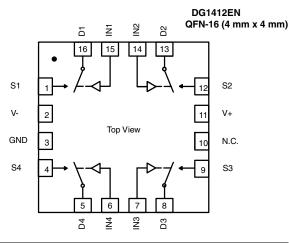
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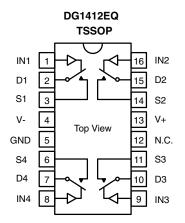
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### FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION - DG1412



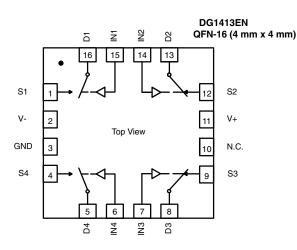
TRUTH TABLE - DG1412					
LOGIC SWITCH					
0	Off				
1	On				



#### Notes

- QFN EXPOSED PAD TIED TO V-
- N.C. = NO CONNECT
- Switches Shown for Logic "0" Input

#### FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION - DG1413



TRUTH TABLE - DG1413						
LOGIC SWITCHES 1, 4 SWITCHES 2, 3						
0	Off	On				
1	On	Off				

DG1413EQ TSSOP IN2 IN1 16 D1 15 D2 2 S1 14 S2 3 13 V+ V-4 GND 5 Top View 12 N.C. S4 11 S3 6 D4 10 D3 7 IN4 8 9 IN3

### Notes

- QFN EXPOSED PAD TIED TO V-
- N.C. = NO CONNECT
- Switches Shown for Logic "0" Input





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DEVICE OPTIONS									
PART NUMBER	CONFIGURATION	SWITCH FUNCTION	TEMPERATURE RANGE	PACKAGE					
DG1411EN-T1-GE4	Quad SPST	NC	-40 °C to +125 °C	QFN (4 mm x 4 mm) 16L (Variation 2)					
DG1412EN-T1-GE4	Quad SPST	NO	-40 °C to +125 °C	QFN (4 mm x 4 mm) 16L (Variation 2)					
DG1413EN-T1-GE4	Quad SPST	NC/NO	-40 °C to +125 °C	QFN (4 mm x 4 mm) 16L (Variation 2)					
DG1411EQ-T1-GE3	Quad SPST	NC	-40 °C to +125 °C	TSSOP-16					
DG1412EQ-T1-GE3	Quad SPST	NO	-40 °C to +125 °C	TSSOP-16					
DG1413EQ-T1-GE3	Quad SPST	NC/NO	-40 °C to +125 °C	TSSOP-16					

ABSOLUTE MAXIMUM RATINGS						
ELECTRICAL PARAMETER	CONDITIONS	LIMITS	UNIT			
V+	Reference to GND	-0.3 V to +25 V				
V-	Reference to GND	+0.3 V to -25 V				
V+ to V-		+35	V			
Analog Inputs (S or D)		V- (-0.3 V) to V+ (+0.3 V)				
Digital Inputs		GND (-0.3 V) to V+ (+0.3 V)				
Maximum Continuous Switch Current	TSSOP-16, T <sub>A</sub> = 25 °C	190				
	QFN (4 mm x 4 mm) 16L, T <sub>A</sub> = 25 °C	250	mA			
	TSSOP-16, T <sub>A</sub> = 125 °C	90				
	QFN (4 mm x 4 mm) 16L, T <sub>A</sub> = 125 °C	100				
Maximum Pulse Switch Current	Pulse at 1 mS, 10 % duty cycle	500	1			
The second Device second	TSSOP-16					
Thermal Resistance	QFN (4 mm x 4 mm) 16L	32	°C/W			
Temperature			•			
Operating Temperature		-40 to 125				
Max. Operating Junction Temperature		150	 ⊃°			
Operating Junction Temperature		125	-0			
Storage Temperature		-65 to 150	1			

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

RECOMMENDED OPERATING RANGE						
ELECTRICAL	MINIMUM	MAXIMUM	UNIT			
IN	± 4.5	± 16.5	V			



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ELECTRICAL CHARACTERISTICS									
PARAMETER	SYMBOL	TEST CONDITIONS UNLESS OTHERWISE SPECIFIED V+ = 15 V, V- = -15 V V <sub>INH</sub> = 2 V, V <sub>INL</sub> = 0.8 V	+25 °C	-40 °C to +85 °C	-40 °C to +125 °C	TYP./MAX.	UNIT		
Analog Switch	•	•							
Analog Signal Range	V <sub>ANALOG</sub>			V- to V+		-	V		
Drain-Source		$V_{\rm S} = \pm 10$ V, $I_{\rm S} = -10$ mA; see fig. 23	1.5	-	-	Тур.	Ω		
On-Resistance	R <sub>DS(on)</sub>	V+ = +13.5 V, V- = -13.5 V	1.8	2.3	2.6	Max.	52		
ON-Resistance Flatness	R <sub>flat(on)</sub>	$V_{\rm S}$ = ± 10 V, I <sub>S</sub> = -10 mA	0.3 0.36	- 0.45	- 0.48	- Max.			
ON-Resistance Matching	$\Delta R_{DS(on)}$		0.08	-	-	Тур.	Ω		
on neolocation matering	DS(on)		0.18	0.19	0.21	Max.			
Switch Off Leakage Current	I <sub>S</sub> /I <sub>d(off)</sub>	V+ = +16.5 V, V- = -16.5 V	± 0.03	-	-	Тур.			
ownon on Lounage our one	15/10(01)	$V_S = \pm 10$ V, $V_D = \pm 10$ V; see fig. 24	± 0.55	± 2	± 12.5	Max.	nA		
Channel On Leakage Current	I <sub>d(on)</sub>	$V_{S} = V_{D} = \pm 10 \text{ V}; \text{ see fig. } 25$	± 0.15	-	-	Тур.	101		
	·u(01)	······································	± 2	± 4	± 35	Max.			
Digital Control	1	1			1	T			
Input, High Voltage	V <sub>INH</sub>		-	-	2	V <sub>min.</sub>	v		
Input, Low Voltage	V <sub>INL</sub>		-	-	0.8	V <sub>max.</sub>			
Input Leakage	I <sub>IN</sub>	V <sub>IN</sub> = V <sub>GND</sub> or V+	0.005	-	-	Тур.	μA		
			-	-	± 0.1	Max.	P.7 1		
Digital Input Capacitance	C <sub>IN</sub>		3.5	-	-	Тур.	pF		
Dynamic Characteristics	1	1		1	1	T	1		
Break-Before-Make Time	topen	$V_{S1} = V_{S2} = 10 V$ , see fig. 31;		-	-	Тур.	Typ. Min.		
		R <sub>L</sub> = 300 Ω, C <sub>L</sub> = 35 pF	-	-	10	Min.			
Turn-On Time	t <sub>ON</sub>		100	-	-	Тур.	ns		
	UN	-011	-011	$V_{\rm S} = 10$ V, see fig. 30	150	170	190	Max.	
Turn-Off Time	t <sub>OFF</sub>	$R_L = 300 \Omega, C_L = 35 pF$	64 120	- 140	- 160	Typ. Max.			
Charge Injection	Q <sub>INj</sub>	$C_L = 1 \text{ nF}, R_{GEN} = 0 \Omega, V_S = 0 V$ see fig. 32	-20	-	-	Тур.	рС		
Off Isolation	OIRR	$C_{L} = 5 \text{ pF}, R_{L} = 50 \Omega, 100 \text{ kHz}$	-80	-	-	Тур.			
Cross Talk	X <sub>TALK</sub>	$C_{L} = 5 \text{ pF}, R_{L} = 50 \Omega, 1 \text{ MHz}$	-100	-	-	Тур.	dB		
Insertion Loss		f = 1 MHz, $R_L$ = 50 Ω, $C_L$ = 5 pF	-0.08	-		Тур.			
Total Harmonic Distortion	THD	R <sub>L</sub> = 110 Ω, 15 V <sub>p-p</sub> , f = 20 Hz to 20 kHz	0.014	-	-	Тур.	%		
Bandwidth, -3dB	BW	$C_L = 5 \text{ pF}, R_L = 50 \Omega$	210	-	-	Тур.	MHz		
Source Off Capacitance	C <sub>S(off)</sub>		11	-	-	Тур.			
Drain Off Capacitance	C <sub>D(off)</sub>	f = 1 MHz, V <sub>S</sub> = 0 V	24	-	-	Тур.	pF		
Drain On Capacitance	C <sub>D(on)</sub>		-	Тур.					
Power Requirements	• • • •	•							
Power Supply Range		GND = 0 V		± 4.5/± 1	6.5 min./ma	x.	V		
		Digital Inputs 0 or V+	0.001	-	-	Тур.			
	1.	V+ = +16.5 V, V- = -16.5 V	-	-	1	Max.	- - μΑ -		
Dower Cupely Comercia	I+		220	-	-	Тур.			
Power Supply Current		IN1 = IN2 = IN3 = IN4 = 5 V	-	-	380	Max.			
	,		0.001	-	-	Тур.			
	I-	Digital Inputs 0 or V+	-	-	1	Max.			



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ELECTRICAL CHARA	ELECTRICAL CHARACTERISTICS - SINGLE 12 V SUPPLY							
PARAMETER	SYMBOL	TEST CONDITION: UNLESS OTHERWISE SP V+ = 12 V, V- = 0 V V <sub>INH</sub> = 2 V, V <sub>INL</sub> = 0.8	ECIFIED	+25 °C	-40 °C to +85 °C	-40 °C to +125 °C	TYP./MAX.	UNIT
Analog Switch								
Analog Signal Range	V <sub>ANALOG</sub>				0 V to V+	•		V
Drain-Source	Base	$V_{\rm S}$ = 0 V to 10 V, $I_{\rm S}$ = -10		2.8	-	-	Тур.	Ω
On-Resistance	R <sub>DS(on)</sub>	see fig. 23, V+ = 10.8 V, V	′- = 0 V	3.5	4.3	4.8	Max.	52
ON-Resistance Flatness	R <sub>flat(on)</sub>	$V_{S} = 0 V$ to 10 V, $I_{S} = -1$	0 mA	0.6	-	-	Тур.	
	· · · iai(on)	vs = 0 v to 10 v, is = 1	0 11 11 1	1.1	1.2	1.3	Max.	Ω
ON-Resistance Matching	$\Delta R_{on}$			0.08	-	-	Тур.	
on noolotanoo matoming				0.21	0.23	0.25	Max.	
Switch Off Lookage Current	1.4	V+ = 10.8 V, V- = 0 V <sub>S</sub> = 1 V/10 V, V <sub>D</sub> = 10 V	V	± 0.02	-	-	Тур.	
Switch Off Leakage Current	I <sub>S</sub> /I <sub>d(off)</sub>	$v_{\rm S} = 10/10$ v, $v_{\rm D} = 10$ see fig. 24	V/U V	± 0.55	± 2	± 12.5	Max.	nA
Channel On Leakage Current		V <sub>S</sub> = V <sub>D</sub> = 1 V/10 V; see 1	lia 05	± 0.15	-	-	Тур.	
Channel On Leakage Current	I <sub>d(on)</sub>	$v_{\rm S} = v_{\rm D} = 1$ v/10 v, see	iig. 25	± 1.5	± 4	± 30	Max.	
Digital Control								
Input, High Voltage	V <sub>INH</sub>			-	-	2	Min.	V
Input, Low Voltage	V <sub>INL</sub>			-	-	0.8	Max.	v
Input Leakage	$I_{\rm IN}$ $V_{\rm IN} = V_{\rm GND}$ or V+		0.001	-	-	Тур.	μA	
Input Leakage				-	-	± 0.1		Max.
Digital Input Capacitance	C <sub>IN</sub>			3.5	-	-	Тур.	pF
Dynamic Characteristics								
Break-Before-Make Time	t <sub>OPEN</sub>	$V_{S1} = V_{S2} = 8 V$ ; see fig		130	-	-	Тур.	
Broak Boloro Mako Amo	OPEN	$R_L = 300 \Omega, C_L = 35$	pF	-	-	40	Min.	
Turn-On Time	t <sub>ON</sub>			210	-	-	Тур.	ns
	V <sub>S</sub> = 8 V; see fig. 30,			250	320	360	Max.	
Turn-Off Time	t <sub>OFF</sub>	$R_L = 300 \Omega, C_L = 35$	pF	80	-	-	Тур.	
	OFF			135	165	190	Max.	
Charge Injection	Q <sub>INj</sub>	$C_L = 1 \text{ nF}, R_{GEN} = 0 \Omega, V_S$ see fig. 32	<sub>S</sub> = 6 V	14	-	-	Тур.	рС
Off Isolation	OIRR		100 kHz	-80	-	-	Тур.	
Cross Talk	X <sub>TALK</sub>	$R_L = 50 \Omega$ , $C_L = 5 pF$	1 MHz	-100	-	-	Тур.	dB
Insertion Loss		f = 1 MHz, $R_L$ = 50 $\Omega$ , $C_L$	= 5 pF	-0.16	-	-	Тур.	
Bandwidth, -3dB	BW	$R_L = 50 \Omega, C_L = 5 p$	F	200	-	-	Тур.	MHz
Source Off Capacitance	C <sub>S(off)</sub>			17	-	-	Тур.	
Drain Off Capacitance	C <sub>D(off)</sub>	f = 1 MHz, V <sub>S</sub> = 6 V	/	30	-	-	Тур.	pF
Drain On Capacitance	C <sub>D(on)</sub>			94	-	-	Тур.	
Power Requirements								
Power Supply Range		GND = 0 V, V- = 0 V	/		± 5/± 16	6.5 min./max		V
		Digital Inputs 0 or V	+	0.001	-	-	Тур.	
Dower Cumply Current		V+ = 13.2 V		-	-	1	Max.	
Power Supply Current	I+		IN1 = IN2 = IN3 = IN4 = 5 V		-	-	Тур.	μA
	IN1 =	11N1 = 11N2 = 11N3 = 11N4 =			-	380	Max.	



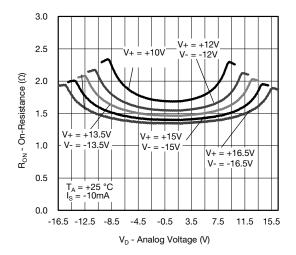
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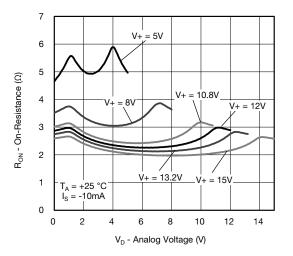
PARAMETER	SYMBOL	TEST CONDITIONS UNLESS OTHERWISE SPE V+ = 5 V, V- = -5 V V <sub>INH</sub> = 2 V, V <sub>INL</sub> = 0.8	CIFIED	+25 °C	-40 °C to +85 °C	-40 °C to +125 °C	TYP./MAX.	UNIT
Analog Switch					•	•		
Analog Signal Range	V <sub>ANALOG</sub>				0 to V+			V
Drain-Source	P	$V_{\rm S}$ = ± 4.5 V, $I_{\rm S}$ = -10 mA; se	e fig. 23,	3.3	-	-	Тур.	
On-Resistance	R <sub>DS(on)</sub>	V+ = +4.5 V, V- = -4.5	V	4	4.9	5.4	Max.	
ON-Resistance Flatness	R <sub>flat(on)</sub>	V <sub>S</sub> = ± 4.5 V, I <sub>S</sub> = -10 n	nΔ	0.9	-	-	Тур.	Ω
	• tiat(on)	V3 - 1 4.0 V, IS - 10 I		1.1	1.24	1.31	Max.	32
ON-Resistance Matching	$\Delta R_{on}$			0.08	-	-	Тур.	
on neolocanoe matering	- in ton			0.22	0.23	0.25	Max.	
Quitab Off Lealuana Quinnant	1.4	$V_{+} = +5.5 V, V_{-} = -5.5 V$		± 0.03	-	-	Тур.	
Switch Off Leakage Current	I <sub>S</sub> /I <sub>d(off)</sub>	V <sub>S</sub> = +/- 4.5 V, V <sub>D</sub> = -/+ 4 see fig. 24	.5 V,	± 0.55	± 2	± 12.5	Max.	nA
Channel On Leakage Current		$VS = VD = \pm 4.5 V$ ; see fig	~ 05	± 0.05	-	-	Тур.	10.4
Channel On Leakage Current	I <sub>d(on)</sub>	$V3 = VD = \pm 4.5 V$ , see in	y. 25	± 1	± 4	± 30	Max.	
Digital Control				_		_		
Input, High Voltage	V <sub>INH</sub>			-	-	2	Min.	v
Input, Low Voltage	V <sub>INL</sub>			-	-	0.8	Max.	v
Input Leakage	l	V <sub>IN</sub> = V <sub>GND</sub> or V+		0.001	-	-	Тур.	μA
Input Leakage	I <sub>IN</sub>	VIN = VGND OI V+			-	± 0.1	Max.	μn
Digital Input Capacitance	C <sub>IN</sub>			3.5	-	-	Тур.	pF
Dynamic Characteristics								
Break-Before-Make Time	t <sub>OPEN</sub>	$V_{S1} = V_{S2} = 3 V$ ; see fig.		150	-	-	Тур.	
Dieak-Deloie-Make Time	OPEN	$R_L = 300 \Omega, C_L = 35 p$	F	-	-	50	Min.	
Turn-On Time	tou			300	-	-	Тур.	ns
rum-on nime	t <sub>on</sub>	V <sub>S</sub> = 3 V; see fig. 30,		400	465	510	Max.	115
Turn-Off Time		$R_L = 300 \Omega, C_L = 35 p$	F	150	-	-	Тур.	
Tum-On Time	t <sub>OFF</sub>			290	320	380	Max.	
Charge Injection	Q <sub>INj</sub>	$C_L$ = 1 nF, $R_{GEN}$ = 0 $\Omega$ , $V_S$ see fig. 32	= 0 V;	22	-	-	Тур.	рС
Off Isolation	OIRR		100 KHz	-80	-	-	Тур.	
Cross Talk	X <sub>TALK</sub>	$R_L = 50 \Omega$ , $C_L = 5 pF$	1 MHz	-100	-	-	Тур.	dB
Insertion Loss		f = 1 MHz, $R_L$ = 50 $\Omega$ , $C_L$ =	= 5 pF	-0.19	-	-	Тур.	
Bandwidth, -3dB	BW	$R_L = 50 \Omega, C_L = 5 pF$		200	-	-	Тур.	MHz
Source Off Capacitance	C <sub>S(off)</sub>			18	-	-	Тур.	
Drain Off Capacitance	C <sub>D(off)</sub>	$f = 1 \text{ MHz}, V_S = 0 \text{ V}$		31	-	-	Тур.	pF
Drain On Capacitance	C <sub>D(on)</sub>			95	-	-	Тур.	
Power Requirements								
Power Supply Range		GND = 0 V			± 4.5 V/±	16.5 min./m	ax.	V
	1.	Digital Inputs 0 V or V	+	0.001	-	-	Тур.	
Dower Supply Orment	l+	V+ = +5.5 V, V- = -5.5		-	-	1	Max.	
Power Supply Current			0.001	-	-	Тур.	μA	
	I-	Digital Inputs = 0 V or V	V+	-	-	1	Max.	



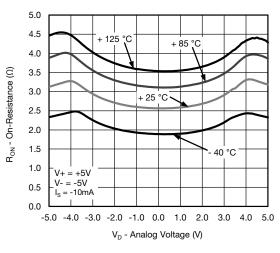
### **TYPICAL CHARACTERISTICS** ( $T_A = 25 \text{ °C}$ , unless otherwise noted)



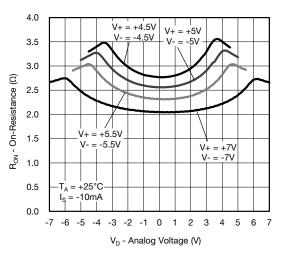
**On-Resistance vs. Analog Voltage (DS1)** 



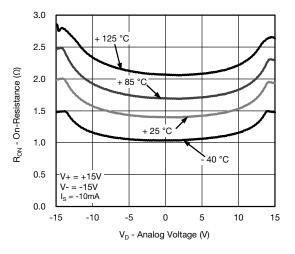
On-Resistance vs. Analog Voltage (DSS)



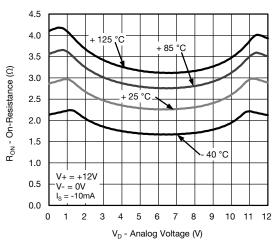
On-Resistance vs. Temperature (± 5 V)



**On-Resistance vs. Analog Voltage (DS2)** 



On-Resistance vs. Temperature (± 15 V)



On-Resistance vs. Temperature (+12 V)

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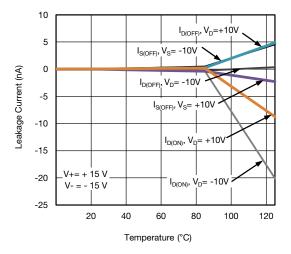
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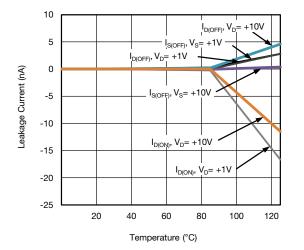


**Vishay Siliconix** 

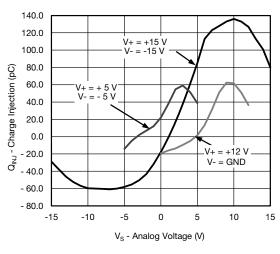
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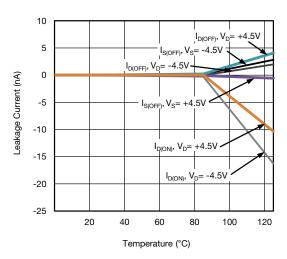
Leakage Current vs. Temperature (± 15 V)



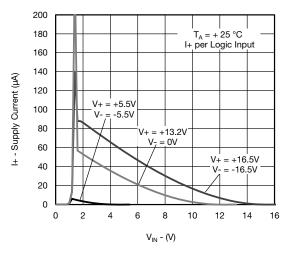
Leakage Current vs. Temperature (+12 V)



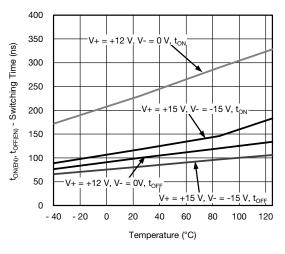
**Charge Injection vs. Analog Voltage** 



Leakage Current vs. Temperature (± 5 V)



Supply Current vs. Logic Level



Switching Time vs. Temperature

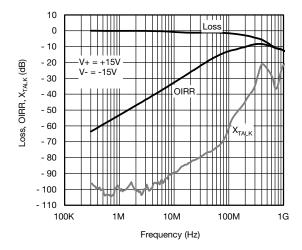
8

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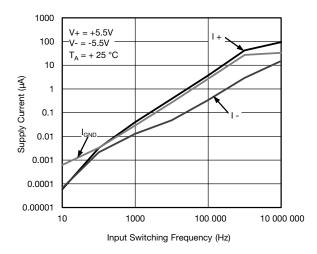
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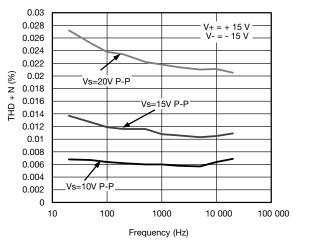
### **TYPICAL CHARACTERISTICS** ( $T_A = 25 \text{ °C}$ , unless otherwise noted)



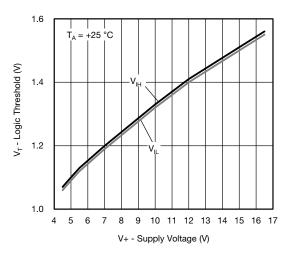
BW, OIRR, X<sub>TALK</sub> vs. Frequency



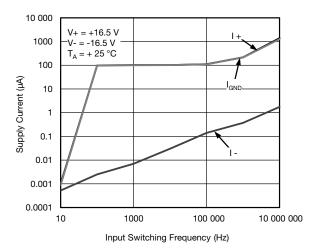
Supply Current vs. Switching Frequency (± 5.5 V)



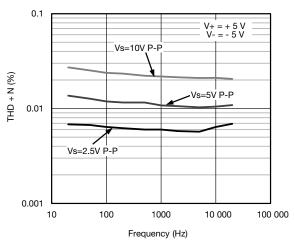
THD vs. Frequency (± 15 V)



Logic Threshold vs. Supply Voltage



Supply Current vs. Switching Frequency (± 16.5 V)



THD vs. Frequency (± 5 V)

S13-2467-Rev. B, 02-Dec-13

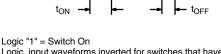
9

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0.9 x V<sub>OUT</sub> Switch

VINH



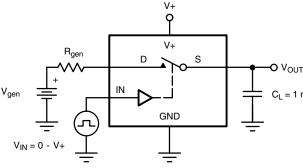
Logic input waveforms inverted for switches that have the opposite logic sense.



VOUT

IN

On



IN depends on switch configuration: input polarity determined by sense of switch.

Off

 $Q = V_{OUT} \times C_L$ 

VOUT



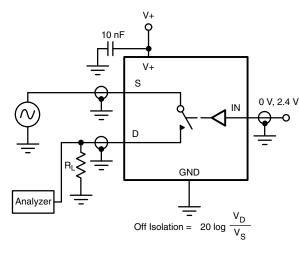
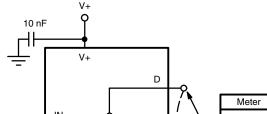


Fig. 3 - Off-Isolation



HP4192A 0 V, 2.4 V O Impedance Analyzer r Equívalent S GND f = 1 MHz

Fig. 4 - Channel Off/On Capacitance

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Document Number: 62749

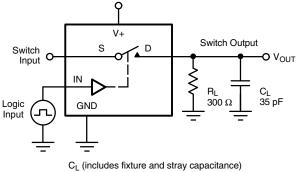
## DG1411, DG1412, DG1413

**Vishay Siliconix** 

 $t_r < 5 \text{ ns}$ 

On

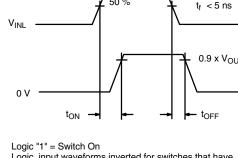




 $V_{OUT} = V_D \left(\frac{R_L}{R_L + R_{ON}}\right)$ 

V+





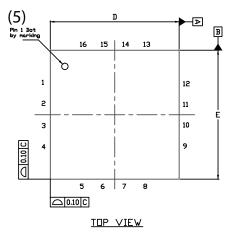
50 %

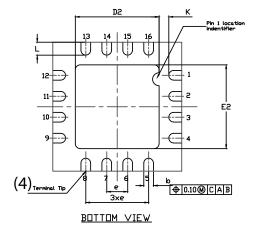
Logic Input

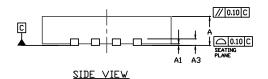
Output



QFN 4x4-16L Case Outline







**VARIATION 1 VARIATION 2** MILLIMETERS(1) MILLIMETERS(1) DIM INCHES INCHES MIN. NOM. MAX. MIN. NOM. MAX. MIN. NOM. MAX. MIN. NOM. MAX. 0.75 0.85 0.95 0.029 0.033 0.037 0.75 0.85 0.95 0.029 0.033 0.037 А 0 -0.05 0 0.002 0 0.05 \_ 0.002 A1 -\_ 0 A3 0.20 ref. 0.008 ref. 0.20 ref. 0.008 ref. b 0.25 0.30 0.35 0.010 0.012 0.014 0.25 0.30 0.35 0.010 0.012 0.014 4.00 BSC D 0.157 BSC 4.00 BSC 0.157 BSC 0.087 0.106 2.1 2.2 0.083 2.6 2.7 0.102 D2 2.0 0.079 2.5 0.098 0.65 BSC 0.026 BSC 0.65 BSC 0.026 BSC е Е 4.00 BSC 0.157 BSC 4.00 BSC 0.157 BSC 0.087 2.1 2.2 0.083 2.7 0.102 0.106 2.6 E2 2.0 0.079 2.5 0.098 0.20 min. 0.008 min 0.20 min. 0.008 min. Κ 0.5 0.7 0.020 0.024 0.028 0.5 0.016 0.020 L 0.6 0.3 0.4 0.012 N<sup>(3)</sup> 16 16 16 16 Nd<sup>(3)</sup> 4 4 4 4 Ne<sup>(3)</sup> 4 4 4 4

#### Notes

<sup>(1)</sup> Use millimeters as the primary measurement.

<sup>(2)</sup> Dimensioning and tolerances conform to ASME Y14.5M. - 1994.

<sup>(3)</sup> N is the number of terminals. Nd and Ne is the number of terminals in each D and E site respectively.

<sup>(4)</sup> Dimensions b applies to plated terminal and is measured between 0.15 mm and 0.30 mm from terminal tip.

<sup>(5)</sup> The pin 1 identifier must be existed on the top surface of the package by using identification mark or other feature of package body.

<sup>(6)</sup> Package warpage max. 0.05 mm.

ECN: S13-0893-Rev. B, 22-Apr-13 DWG: 5890

1

Document Number: 71921

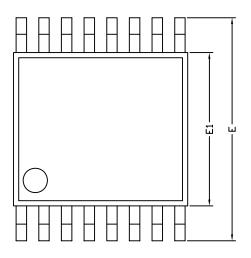
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# Package Information

Vishay Siliconix

### TSSOP: 16-LEAD





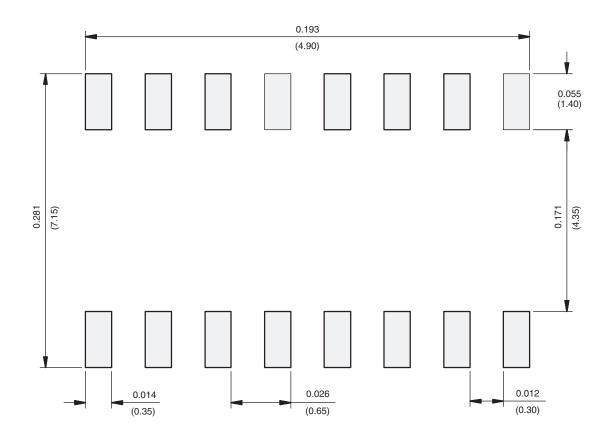
	C	DIMENSIONS IN MILLIMETERS					
Symbols	Min	Min Nom					
A	-	1.10	1.20				
A1	0.05	0.10	0.15				
A2	-	1.00	1.05				
В	0.22	0.28	0.38				
С	-	0.127	-				
D	4.90	5.00	5.10				
E	6.10	6.40	6.70				
E1	4.30	4.40	4.50				
е	-	0.65	-				
L	0.50	0.60	0.70				
L1	0.90	1.00	1.10				
у	-	-	0.10				
θ1	0°	3°	6°				
ECN: S-61920-Rev. D, 23 DWG: 5624	-Oct-06						



**PAD** Pattern

Vishay Siliconix

#### **RECOMMENDED MINIMUM PAD FOR TSSOP-16**



Recommended Minimum Pads Dimensions in inches (mm)



Vishay

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